

Ordering number : ENN6997

N-Channel Silicon MOSFET



**CPH3407**

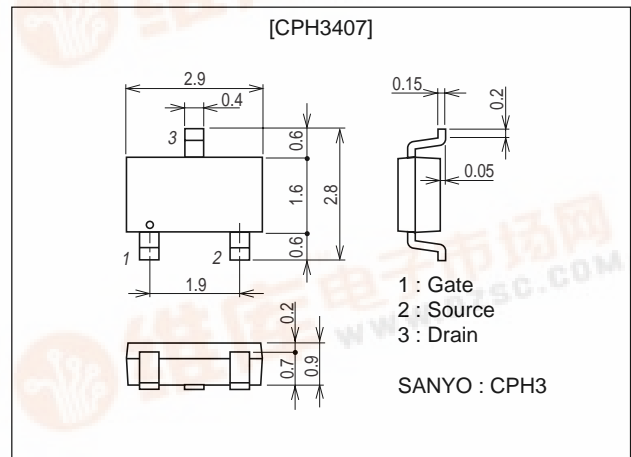
**Ultrahigh-Speed Switching Applications**

**Features**

- Low ON-resistance.
- Ultrahigh-speed switching.
- 2.5V drive.

**Package Dimensions**

unit : mm  
2152A



**Specifications**

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		20	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±10	V
Drain Current (DC)	I <sub>D</sub>		5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	20	A
Allowable Power Dissipation	P <sub>D</sub>	Mounted on a ceramic board (900mm <sup>2</sup> ×0.8mm)	1.2	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =1mA, V <sub>GS</sub> =0	20			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0			1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =3A	7	10		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =3A, V <sub>GS</sub> =4V		28	37	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =1A, V <sub>GS</sub> =2.5V		35	50	mΩ

Marking : KG

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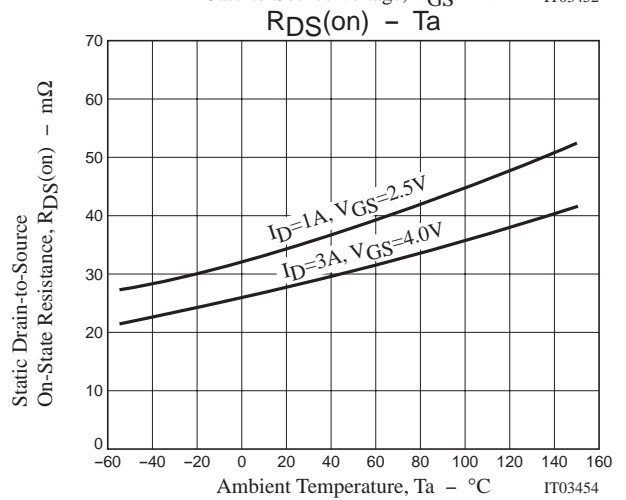
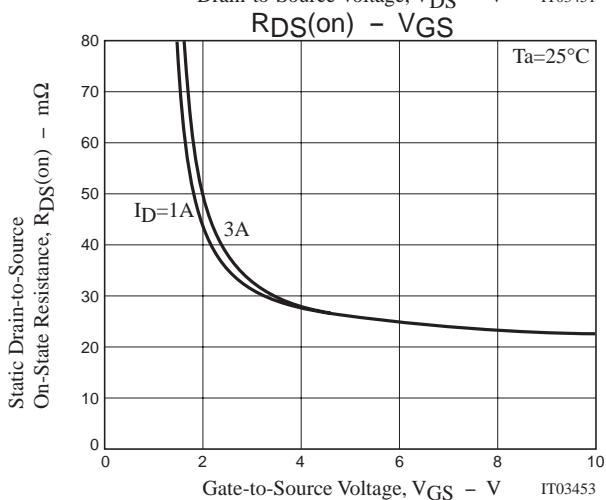
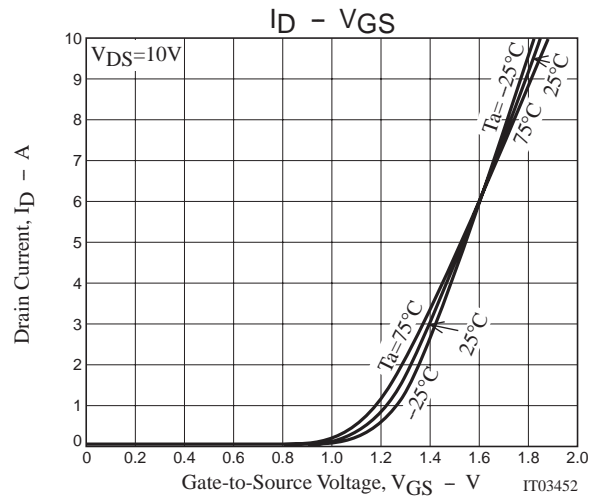
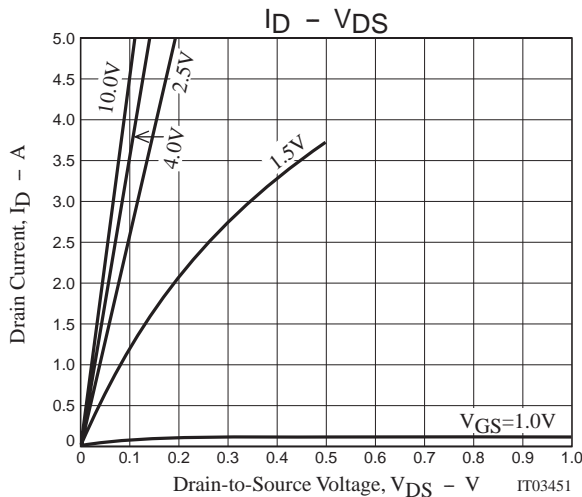
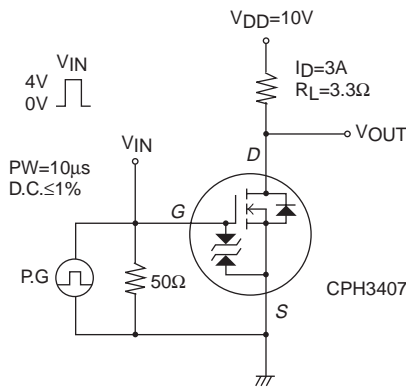


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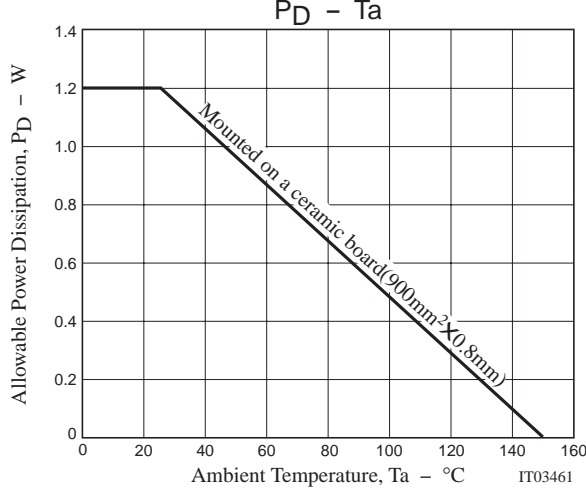
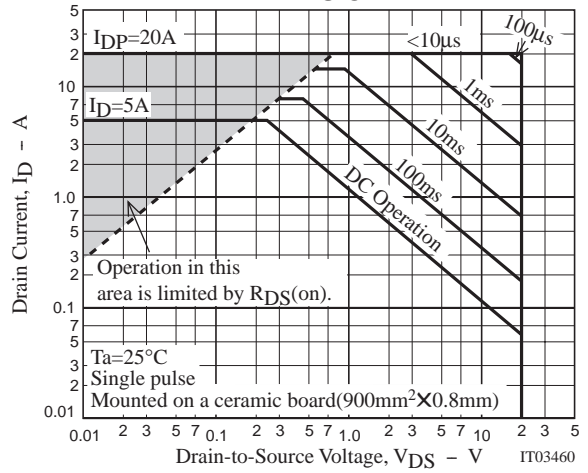
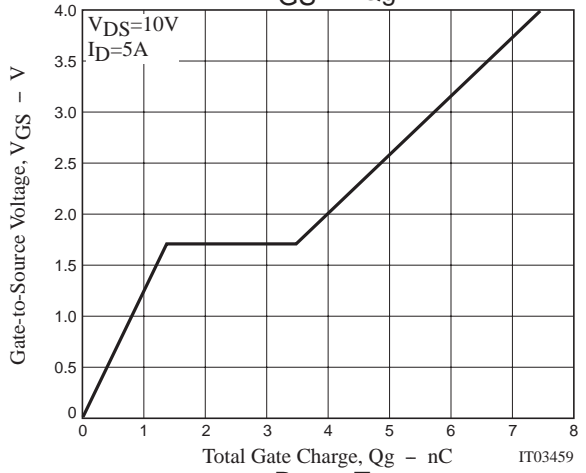
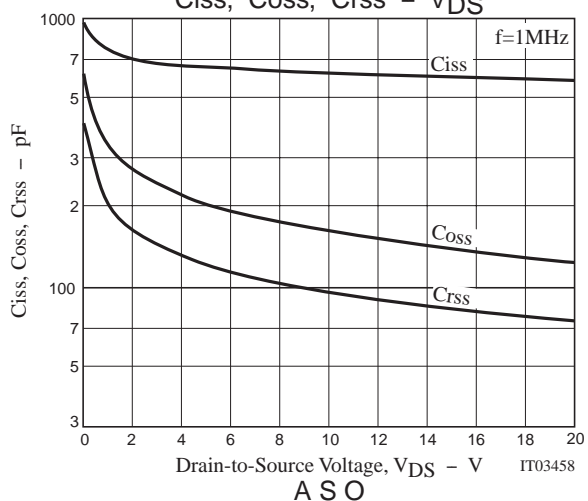
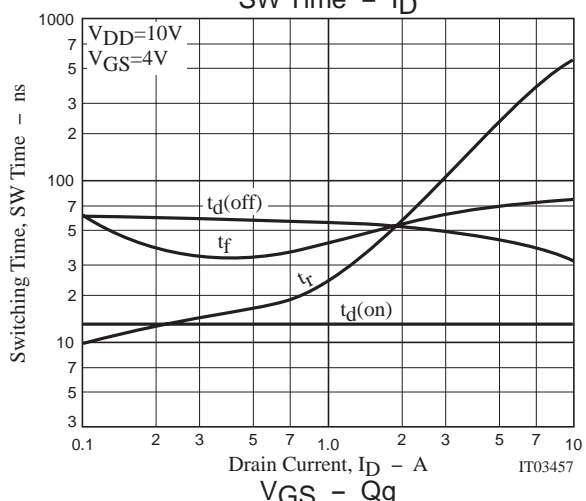
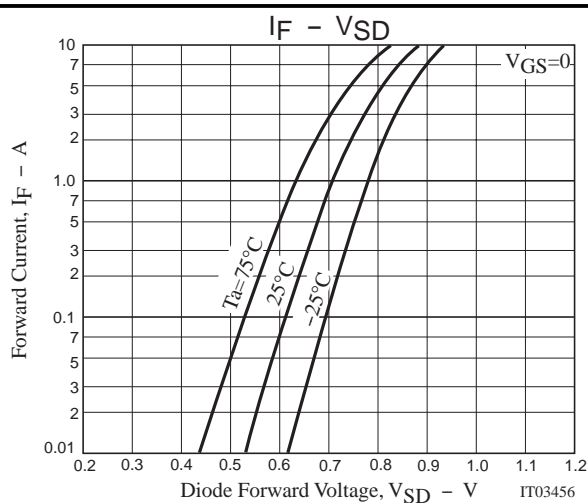
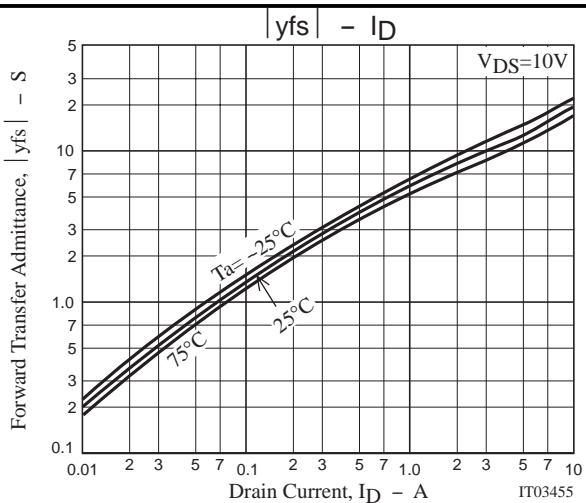
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	$C_{iss}$	$V_{DS}=10V, f=1MHz$		630		pF
Output Capacitance	$C_{oss}$	$V_{DS}=10V, f=1MHz$		160		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS}=10V, f=1MHz$		95		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit		13		ns
Rise Time	$t_r$	See specified Test Circuit		110		ns
Turn-OFF Delay Time	$t_d(off)$	See specified Test Circuit		47		ns
Fall Time	$t_f$	See specified Test Circuit		65		ns
Total Gate Charge	$Q_g$	$V_{DS}=10V, V_{GS}=4V, I_D=5A$		7.3		nC
Gate-to-Source Charge	$Q_{gs}$	$V_{DS}=10V, V_{GS}=4V, I_D=5A$		1.4		nC
Gate-to-Drain "Miller" Charge	$Q_{gd}$	$V_{DS}=10V, V_{GS}=4V, I_D=5A$		2.1		nC
Diode Forward Voltage	$V_{SD}$	$I_S=5A, V_{GS}=0$		0.8	1.2	V

## Switching Time Test Circuit



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